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JUL 03 2007

Amendment under 37 C.F.R. 1.114

Serial No. 10/713,219

Page 2

AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) A method for fabricating a thin film transistor, comprising:

forming a first amorphous semiconductor film;

forming a material including a metal element to promote crystallization over the first amorphous semiconductor film;

heating the first amorphous semiconductor film to form a first crystalline semiconductor film;

forming a second amorphous semiconductor film over the first crystalline semiconductor film by sputtering while a magnetic field is applied to a target using a magnet;

heating the first crystalline semiconductor film and the second amorphous semiconductor film; and

removing the second amorphous semiconductor film, wherein the second amorphous semiconductor film serves as a gettering sink, and

wherein the second amorphous semiconductor film comprises nitrogen at a concentration of 1×10^{18} atoms/cm³ or lower, oxygen at a concentration of 8×10^{19} atoms/cm³ or lower, and noble gas at a concentration of 1×10^{20} atoms/cm³ or higher.

2. (Withdrawn) A method for fabricating a thin film transistor, comprising:

forming a first amorphous semiconductor film;

forming a material including a metal element to promote crystallization over the first amorphous semiconductor film;

forming a first crystalline semiconductor film by heating the first amorphous semiconductor film;

irradiating the first crystalline semiconductor film with a laser beam;

forming a second amorphous semiconductor film over the first crystalline semiconductor film;

10639920.1

Amendment under 37 C.F.R. 1.114
Serial No. 10/713,219
Page 3

heating the first crystalline semiconductor film and the second amorphous semiconductor film;

removing the second amorphous semiconductor film; and

wherein the amorphous semiconductor film contains nitrogen concentration is 1×10^{18} atoms/cm³ or lower, oxygen concentration is 8×10^{19} atoms/cm³ or lower, and noble gas concentration is 1×10^{20} atoms/cm³ or higher.

3. (Currently Amended) A method for fabricating a thin film transistor, comprising:

forming a first amorphous semiconductor film;

forming a material including a metal element to promote crystallization over the first amorphous semiconductor film;

forming a second amorphous semiconductor film over the first amorphous semiconductor film by sputtering while a magnetic field is applied to a target using a magnet;

heating the first amorphous semiconductor film and the second amorphous semiconductor film; and

removing the second amorphous semiconductor film ,

wherein the second amorphous semiconductor film serves as a gettering sink, and

wherein the second amorphous semiconductor film comprises nitrogen at a concentration of 1×10^{18} atoms/cm³ or lower, oxygen at a concentration of 8×10^{19} atoms/cm³ or lower, and noble gas at a concentration of 1×10^{20} atoms/cm³ or higher.

4. (Withdrawn) A method for fabricating a thin film transistor, comprising:

forming a first amorphous semiconductor film;

forming a material including a metal element to promote crystallization over the first amorphous semiconductor film;

forming a first crystalline semiconductor film by heating the first amorphous semiconductor film;

forming a second amorphous semiconductor film over the first crystalline semiconductor film;

Amendment under 37 C.F.R. 1.114
Serial No. 10/713,219
Page 4

RECEIVED
CENTRAL FAX CENTER

JUL 03 2007

moving the metal element into the second amorphous semiconductor film by heating the first crystalline semiconductor film and the second amorphous semiconductor film;

removing the second amorphous semiconductor film; and

wherein the second amorphous semiconductor film contains nitrogen concentration is 1×10^{18} atoms/cm³ or lower, oxygen concentration is 8×10^{19} atoms/cm³ or lower, and noble gas concentration is 1×10^{20} atoms/cm³ or higher.

5. (Withdrawn) A method for fabricating a thin film transistor: comprising:

forming a first amorphous semiconductor film;

forming a material including a metal element to promote crystallization over the first amorphous semiconductor film;

forming a first crystalline semiconductor film by heating the first amorphous semiconductor film;

forming a second amorphous semiconductor film over the first crystalline semiconductor film;

performing gettering by heating the first crystalline semiconductor film and the second amorphous semiconductor film;

removing the second amorphous semiconductor film; and

wherein the amorphous semiconductor film contains nitrogen concentration is 1×10^{18} atoms/cm³ or lower, oxygen concentration is 8×10^{19} atoms/cm³ or lower, and noble gas concentration is 1×10^{20} atoms/cm³ or higher.

6. (Withdrawn) A method for fabricating a thin film transistor, comprising:

forming a first amorphous semiconductor film;

forming a material including a metal element to promote crystallization over the first amorphous semiconductor film;

forming a first crystalline semiconductor film by heating the first amorphous semiconductor film;

forming a barrier film over the first crystalline semiconductor film;

forming a second amorphous semiconductor film over the barrier film;

Amendment under 37 C.F.R. 1.114
Serial No. 10/713,219
Page 5

heating the first crystalline semiconductor film and the second amorphous semiconductor film;

removing the second amorphous semiconductor film and the barrier film, and

wherein the second amorphous semiconductor film contains nitrogen concentration is 1×10^{18} atoms/cm³ or lower, oxygen concentration is 8×10^{19} atoms/cm³ or lower, and noble gas concentration is 1×10^{20} atoms/cm³ or higher.

7. (Withdrawn) A method for fabricating a thin film transistor according to Claim 6, wherein the barrier film is an oxide film made by using ozone water or a mixed solution of hydrogen peroxide solution and sulfuric acid, hydrochloric acid or nitric acid.

8. (Canceled)

9. (Withdrawn) A method for fabricating a thin film transistor according to claim 2, wherein the second amorphous semiconductor film is formed by sputtering.

10. (Canceled)

11. (Withdrawn) A method for fabricating a thin film transistor according to claim 4, wherein the second amorphous semiconductor film is formed by sputtering.

12. (Withdrawn) A method for fabricating a thin film transistor according to claim 5,
wherein the second amorphous semiconductor film is formed by sputtering.

13. (Withdrawn) A method for fabricating a thin film transistor according to claim 6,
wherein the second amorphous semiconductor film is formed by sputtering.

14. (Withdrawn) A method for fabricating a thin film transistor, comprising:
forming a first amorphous semiconductor film;

10639920.1

Amendment under 37 C.F.R. 1.114
Serial No. 10/713,219
Page 6

forming a material including a metal element to promote crystallization over the first amorphous semiconductor film;

forming a first crystalline semiconductor film by heating the first amorphous semiconductor film;

forming a second amorphous semiconductor film over the first crystalline semiconductor film;

heating the first crystalline semiconductor film and the second amorphous semiconductor film;

removing the second amorphous semiconductor film;

wherein the second amorphous semiconductor film is formed by sputtering in a state in which a flammable gas and a noble gas are supplied to a film formation chamber, oxygen concentration in the film formation chamber is reduced, and the supply of the flammable gas is stopped; and

wherein the second amorphous semiconductor film contains nitrogen concentration is 1×10^{18} atoms/cm³ or lower, oxygen concentration is 8×10^{19} atoms/cm³ or lower, and noble gas concentration is 1×10^{20} atoms/cm³ or higher.

15. (Withdrawn) A method for fabricating a thin film transistor according to Claim 14, wherein the flammable gas is one element or more elements selected from a group consisting of SiH₄, Si₂H₆, SiH₂Cl₂, SiHCl₃, SiCl₄, GeH₄, PH₃, B₂H₆, AsH₃, and H₂Se.

16. (Withdrawn) A method for fabricating a thin film transistor, comprising:

forming a first amorphous semiconductor film;

forming a material including a metal element to promote crystallization over the first amorphous semiconductor film;

forming a first crystalline semiconductor film by heating the first amorphous semiconductor film;

forming a second amorphous semiconductor film over the first crystalline semiconductor film;

heating the first crystalline semiconductor film and the second amorphous semiconductor film;

10639920.1

Amendment under 37 C.F.R. 1.114
Serial No. 10/713,219
Page 7

removing the second amorphous semiconductor film;

wherein the second amorphous semiconductor film is formed by sputtering in a state in which a filament including Ti that is disposed in a film formation chamber is heated, oxygen concentration in the film formation chamber is reduced, and the heating of the filament is stopped; and

wherein the second amorphous semiconductor film contains nitrogen concentration is 1×10^{18} atoms/cm³ or lower, oxygen concentration is 8×10^{19} atoms/cm³ or lower, and noble gas concentration is 1×10^{20} atoms/cm³ or higher.

17. (Withdrawn) A method for fabricating a thin film transistor, comprising:

forming a first amorphous semiconductor film;

forming a material including a metal element to promote crystallization over the first amorphous semiconductor film;

forming a first crystalline semiconductor film by heating the first amorphous semiconductor film;

forming a second amorphous semiconductor film over the first crystalline semiconductor film;

heating the first crystalline semiconductor film and the second amorphous semiconductor film;

removing the second amorphous semiconductor film;

wherein the second amorphous semiconductor film is formed by sputtering in a state in which a voltage is applied between electrodes including Ti disposed in a film formation chamber to generate a plasma, oxygen concentration in the film formation chamber is reduced, and applying the voltage between the electrodes is stopped; and

wherein the second amorphous semiconductor film contains nitrogen concentration is 1×10^{18} atoms/cm³ or lower, oxygen concentration is 8×10^{19} atoms/cm³ or lower, and noble gas concentration is 1×10^{20} atoms/cm³ or higher.

18. (Currently Amended) A method for fabricating a thin film transistor according to claim 1, wherein the second amorphous semiconductor film is removed by wet etching using hydrazine or tetramethyl ammonium ~~ammonium~~ hydroxide.

10639920.1

Amendment under 37 C.F.R. 1.114
Serial No. 10/713,219
Page 8

19. (Withdrawn) A method for fabricating a thin film transistor according to claim 2, wherein the second amorphous semiconductor film is removed by dry etching using hydrazine or tetramethyl ammonium hydroxide.

20. (Previously presented) A method for fabricating a thin film transistor according to claim 3, wherein the second amorphous semiconductor film is removed by wet etching using hydrazine or tetramethyl ammonium hydroxide.

21. (Withdrawn) A method for fabricating a thin film transistor according to claim 4, wherein the second amorphous semiconductor film is removed by dry etching using hydrazine or tetramethyl ammonium hydroxide.

22. (Withdrawn) A method for fabricating a thin film transistor according to claim 5, wherein the second amorphous semiconductor film is removed by dry etching using hydrazine or tetramethyl ammonium hydroxide.

23. (Withdrawn) A method for fabricating a thin film transistor according to claim 6, wherein the second amorphous semiconductor film is removed by dry etching using hydrazine or tetramethyl ammonium hydroxide.

24. (Withdrawn) A method for fabricating a thin film transistor according to claim 14, wherein the second amorphous semiconductor film is removed by dry etching using hydrazine or tetramethyl ammonium hydroxide.

25. (Withdrawn) A method for fabricating a thin film transistor according to claim 16, wherein the second amorphous semiconductor film is removed by dry etching using hydrazine or tetramethyl ammonium hydroxide.

Amendment under 37 C.F.R. 1.114
Serial No. 10/713,219
Page 9

26. (Withdrawn) A method for fabricating a thin film transistor according to claim 17, wherein the second amorphous semiconductor film is removed by dry etching using hydrazine or tetramethyl ammonium hydroxide.

27. (Original) A method for fabricating a thin film transistor according to claim 1, wherein the noble gas element is one element or more elements selected from a group consisting of helium (He), neon (Ne), argon (Ar), krypton (Kr), and xenon (Xe).

28. (Withdrawn) A method for fabricating a thin film transistor according to claim 2, wherein the noble gas element is one element or more elements selected from a group consisting of helium (He), neon (Ne), argon (Ar), krypton (Kr), and xenon (Xe).

29. (Original) A method for fabricating a thin film transistor according to claim 3, wherein the noble gas element is one element or more elements selected from a group consisting of helium (He), neon (Ne), argon (Ar), krypton (Kr), and xenon (Xe).

30. (Withdrawn) A method for fabricating a thin film transistor according to claim 4, wherein the noble gas element is one element or more elements selected from a group consisting of: helium (He), neon (Ne), argon (Ar), krypton (Kr), and xenon (Xe).

31. (Withdrawn) A method for fabricating a thin film transistor according to claim 5, wherein the noble gas element is one element or more elements selected from a group consisting of helium (He), neon (Ne), argon (Ar), krypton (Kr), and xenon (Xe).

32. (Withdrawn) A method for fabricating a thin film transistor according to claim 6, wherein the noble gas element is one element or more elements selected from a group consisting of helium (He), neon (Ne), argon (Ar), krypton (Kr), and xenon (Xe).

33. (Withdrawn) A method for fabricating a thin film transistor according to claim 14, wherein the noble gas element is one element or more elements selected from a group consisting of helium (He), neon (Ne), argon (Ar), krypton (Kr), and xenon (Xe).

10639920.1

Amendment under 37 C.F.R. 1.114

Serial No. 10/713,219

Page 10

34. (Withdrawn) A method for fabricating a thin film transistor according to claim 16, wherein the noble gas element is one element or more elements selected from a group consisting of helium (He), neon (Ne), argon (Ar), krypton (Kr), and xenon (Xe).

35. (Withdrawn) A method for fabricating a thin film transistor according to claim 17, wherein the noble gas element is one element or more elements selected from a group consisting of helium (He), neon (Ne), argon (Ar), krypton (Kr), and xenon (Xe).

36. (Original) A method for fabricating a thin film transistor according to claim 1, wherein the metal element is one element or more elements selected from a group consisting of iron (Fe), nickel (Ni), cobalt (Co), ruthenium (Ru), rhodium (Rh), palladium (Pd), osmium (Os), iridium (Ir), platinum (Pt), copper (Cu), and gold (Au).

37. (Withdrawn) A method for fabricating a thin film transistor according to claim 2, wherein the metal element is one element or more elements selected from a group consisting of iron (Fe), nickel (Ni), cobalt (Co), ruthenium (Ru), rhodium (Rh), palladium (Pd), osmium (Os), iridium (Ir), platinum (Pt), copper (Cu), and gold (Au).

38. (Original) A method for fabricating a thin film transistor according to claim 3, wherein the metal element is one element or more elements selected from a group consisting of iron (Fe), nickel (Ni), cobalt (Co), ruthenium (Ru), rhodium (Rh), palladium (Pd), osmium (Os), iridium (Ir), platinum (Pt), copper (Cu), and gold (Au).

39. (Withdrawn) A method for fabricating a thin film transistor according to claim 4, wherein the metal element is one element or more elements selected from a group consisting of iron (Fe), nickel (Ni), cobalt (Co), ruthenium (Ru), rhodium (Rh), palladium (Pd), osmium (Os), iridium (Ti), platinum (Pt), copper (Cu), and gold (Au).

40. (Withdrawn) A method for fabricating a thin film transistor according to claim 5, wherein the metal element is one element or more elements selected from a group

10639920.1

Amendment under 37 C.F.R. 1.114
Serial No. 10/713,219
Page 11

consisting of iron (Fe), nickel (Ni), cobalt (Co), ruthenium (Ru), rhodium (Rh), palladium (Pd), osmium (Os), iridium (Ir), platinum (Pt), copper (Cu), and gold (Au).

41. (Withdrawn) A method for fabricating a thin film transistor according to claim 6, wherein the metal element is one element or more elements selected from a group consisting of iron (Fe), nickel (Ni), cobalt (Co), ruthenium (Ru), rhodium (Rh), palladium (Pd), osmium (Os), iridium (Ir), platinum (Pt), copper (Cu), and gold (Au).

42. (Withdrawn) A method for fabricating a thin film transistor according to claim 14, wherein the metal element is one element or more elements selected from a group consisting of iron (Fe), nickel (Ni), cobalt (Co), ruthenium (Ru), rhodium (Rh), palladium (Pd), osmium (Os), iridium (Ir), platinum (Pt), copper (Cu), and gold (Au).

43. (Withdrawn) A method for fabricating a thin film transistor according to claim 16, wherein the metal element is one element or more elements selected from a group consisting of iron (Fe), nickel (Ni), cobalt (Co), ruthenium (Ru), rhodium (Rh), palladium (Pd), osmium (Os), iridium (Ti), platinum (Pt), copper (Cu), and gold (Au).

44. (Withdrawn) A method for fabricating a thin film transistor according to claim 17, wherein the metal element is one element or more elements selected from a group consisting of iron (Fe), nickel (Ni), cobalt (Co), ruthenium (Ru), rhodium (Rh), palladium (Pd), osmium (Os), iridium (Ir), platinum (Pt), copper (Cu), and gold (Au).